PCN Number: 20140421001 PCN Date: 04/28/2014							
Title: Qualification of TSMC F10 as an additional Wafer Fab site for CC2541 devices							
Customer Contact:PCN ManagerPhone:+1(214)480-6037Dept:Quality Services							
*Proposed 1 st Ship Date:	oosed 1 st Ship Date: 07/28/2014		e Date Provided at Sample request				
Change Type: 07/20/2014 Availability: Sample request							
Assembly Site	Assembly Process Assembly Materials						
Design		Specification	Mechanical Specification				
Test Site		hipping/Labeling	Test Process				
☐ Wafer Bump Site☑ Wafer Fab Site		mp Material Materials	Wafer Bump Process				
		per change					
		N Details					
Description of Change:							
This change notification is to announce the addition of TSMC-F10 (Fab 10) as an additional Wafer Fab site option for the products listed in the product affected section of this document.Current Wafer Fab SiteAdditional Wafer Fab Site							
Site/Process/Wafer Diame	or						
TSMC-WFT/0.18UM TSMC			Site/Process/Wafer Diameter TSMC-F10/0.18UM TSMC Process/200mm				
13MC-WF1/0.180M 13MC	100000000000000000000000000000000000000	15MC-F10/0.180	IM ISMC PIOCESS/2001111				
Reason for Change:							
Continuity of supply.							
	rm, Fit, Functior	n, Quality or Reliab	ility (positive / negative):				
None							
Changes to product iden	ification resulti	ng from this PCN:					
Current							
Chip Site	Chip site	e code (20L)	Chip country code (21L)				
TSMC-WFT		T13 USA					
Additional							
Chip Site	Chip site	Chip site code (20L) Chip country					
TSMC-F10	TSS CHN						
Sample Product Shipping Label (not actual product label) TEXAS INSTRUMENTS G4 2DC: 2Q: MSL 2 /260C/1 YEAR SEAL DT OPT: ITEM: 39 LBL: 5A (L)T0:1750 (not actual product label) (1P) SN74LS07NSR (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY (1T) 7523483SI2 (P) (2P) REV: (V) 0033317 (20L) CS0: SHE (21L) CCO:USA (21L) AS0: MLA (23L) ACO: MYS							

Product Affected:				
CC2541CRHA	CC2541F128RHAT	CC2541F256RHAT	HPA01215RHAR	
CC2541CRHAR	CC2541F256RHAR	CC2541F256YS	HPA01216RHAR	
CC2541F128RHAR				

Qualification Data: Approved 4/2/2014							
This qualification has been developed for the validation of this change. The qualification data will							
	validate that the proposed change meets the applicable released technical specifications.						
			1260RGZ (MSL LEVEL				
		C Fab 10	Wafer Fab Process:	ISMC 0.18	UM		
		200mm					
Qualification: Plan I Test Results							
Reliability Test		Conditions		Sample Size / Fail Lot#1 Lot#2 Lot#3			
Latch-up		Per JESD78		6/0	6/0	6/0	
Biased Temperature and Humid	dity	85C/85%R	H (1000 hours)	26/0	26/0	26/0	
**Unbiased HAST		110C/85%	RH (264 hours)	77/0	77/0	77/0	
**Temp Cycle		-55/125C (1000 cycles)	77/0	77/0	77/0	
**High Temp Storage Bake		150C (1000) hours)	77/0	77/0	77/0	
Electrical Characterization	Per datashe	Pass	Pass	Pass			
ESD HBM	+/-1000V			3/0	-	-	
ESD CDM		+/-250V	3/0	-	-		
**Preconditioning: Level 3-260C							
Qualification Data: Approved 1/25/2013							
This qualification has been developed for the validation of this change. The qualification data will							
validate that the proposed change meets the applicable released technical specifications.							
Qualification Device: CC2544RHB (MSL LEVEL3-260C)							
		C Fab 10	TSMC 0.18	5MC 0.18UM			
Wafer Diameter: 200mm							
Qualification: 🗌 Plan 🛛		st Results				<i>i</i> =	
Reliability Test		Conditions		Sample Size / Fail Lot#1 Lot#2 Lot#3			
		1100/050/1			Lot#3		
**Unbiased HAST		110C/85%	77/0	77/0	77/0		
**High Temp Storage Bake		150C (600	77/0	76/0	76/0		
Latch-up		Per JESD78	18/0	-	-		
**Temp Cycle		-55/+125C	77/0	77/0	76/0		
**Biased Temperature & Humidity		85C/85%RI	26/0	26/0	25/0		
ESD HBM		+/-1000V	3/0 3/0	-	-		
ESD CDM Electrical Characterization	ESD CDM		+/-250V			-	
				Pass			
**Preconditioning: Level 3-260C							

Qualification Data: Approved 10/08/2013									
This qualification has been developed for the validation of this change. The qualification data will									
	validate that the proposed change meets the applicable released technical specifications.								
Qualification Device: CC1200RHB (MSL LEVEL3-260C) Wafer Fab Site: TSMC Fab 10 Wafer Fab Process: TSMC 0.18UM									
Wafer Fab Site: Wafer Diameter:	200n		water Fab	Process:	ISM	SMC 0.18UM			
Qualification: Plan I Test Results						(Eail			
Reliability Test		Conditions				Sample Size / Fail Lot#1 Lot#2 Lot#3			
Operating Life Test		125C (1000) hours)			<u>.017 1</u> 39/0	39/0	38/0	
**Preconditioning: Level 3-26	00	1250 (1000	5 110013)			570	55/0	50/0	
Qualification Data: Approved 04/25/2014									
This qualification has been developed for the validation of this change. The qualification data will							ıta will		
validate that the proposed change meets the applicable released technical specifications.									
		Device: CC2							
Wafer Fab Site:		CFab 11	Wafer Fab	Process:	TSM	SMC 0.18UM			
Wafer Diameter:	200n								
Qualification: Plan	Qualification: 🗌 Plan 🛛 Test Results								
Reliability Test	Conditions				Sample Size / Fail Lot#1 Lot#2 Lot#3				
Operating Life Test	Operating Life Test			125C (408 hours)			77/0	77/0	
**Preconditioning: Level 3-26	. .	125C (408 hours) 77/0 77/0 77/0							
Qualification Plan:									
This qualification has been developed for the validation of this change. The qualification data will validate that the proposed change meets the applicable released technical specifications.									
Qualification Schedule:	Start: 2/25/2014 End:				6/25/2014				
Qualification Device: CC2541RHA (MSL LEVEL3-260C)									
Wafer Fab Site:		C Fab 10		/afer Fab Process: TSMC 0.18UM					
Wafer Diameter:				-	I Clark				
Qualification: Z Plan	Test Results								
Reliability Test Conditions			Sample Size / Fail Lot#1 Lot#2 Lot#3				′ Fail Lot#3		
Electrical Characterization Per d			Per datasheet			-	-	-	
ESD HBM +/-1000						3/0	-	-	
ESD CDM +/-250V						3/0	-	-	
Latch-up		Per JESD78				<u>6/0</u>	-	-	
Flash W/E endurance		105K (20,000 cycles)				L2/0	12/0	12/0	
**Preconditioning: Level 3-260C					,-				

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com